

L Number	Hits	Search Text	DB	Time stamp
7	2407	(method process) with (fill filling) with trench with substrate	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:04
8	319	((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide)	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:04
9	144	(semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))) and gas	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:04
10	61	((semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))) and gas) and teos	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:04
11	25	((semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))) and gas) and teos) and (opening aperture)	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:12
12	2488	438/404,405,421,424.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:13
13	8	(((semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))) and gas) and teos) and (opening aperture)) and 438/404,405,421,424.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:13
14	2	6214698.URPN.	USPAT	2004/10/30 18:15
15	12	("4506435" "4740480" "5099304" "5225358" "5674773" "5741740" "5811345" "5902127" "5960300" "5963840" "5976947" "5989977").PN.	USPAT	2004/10/30 18:15
16	446	438/435.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:23
17	5	(((semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))) and gas) and teos) and (opening aperture)) and 438/435.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:23
-	811248	semiconductor	USPAT; US-PGPUB; EPO; JPO	2004/10/22 15:33
-	2185	(method process) with (fill filling) with trench with substrate	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:03
-	34073	semiconductor same (silicon near2 oxide)	USPAT; US-PGPUB; EPO; JPO	2004/06/28 15:51
-	279	semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))	USPAT; US-PGPUB; EPO; JPO	2004/06/28 15:51
-	25	((semiconductor and (((method process) with (fill filling) with trench with substrate) same (silicon near2 oxide))) and gas) and teos) and chamber	USPAT; US-PGPUB; EPO; JPO	2004/10/30 18:05
-	2	"6489254"	USPAT; US-PGPUB; EPO; JPO;	2004/06/29 10:04
-	2	"20020052128"	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/06/29 10:04
-	6	"6180995"	DERWENT USPAT; US-PGPUB; EPO; JPO	2004/09/07 07:02